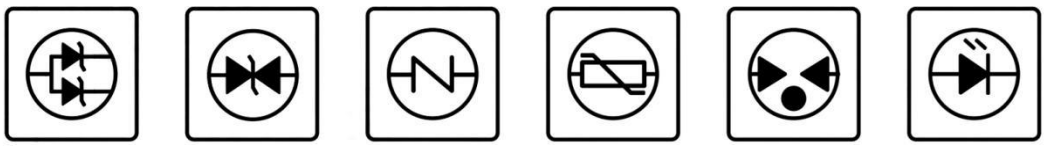
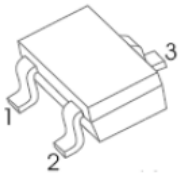
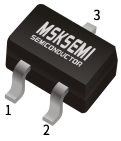
MSKSEMI
SEMICONDUCTOR



Product data sheet





PNP Silicon Epitaxial Planar Transistor

1. BASE
2. EMITTER
3. COLLECTOR

SOT-323

for switching and amplifier applications

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to +150	°C

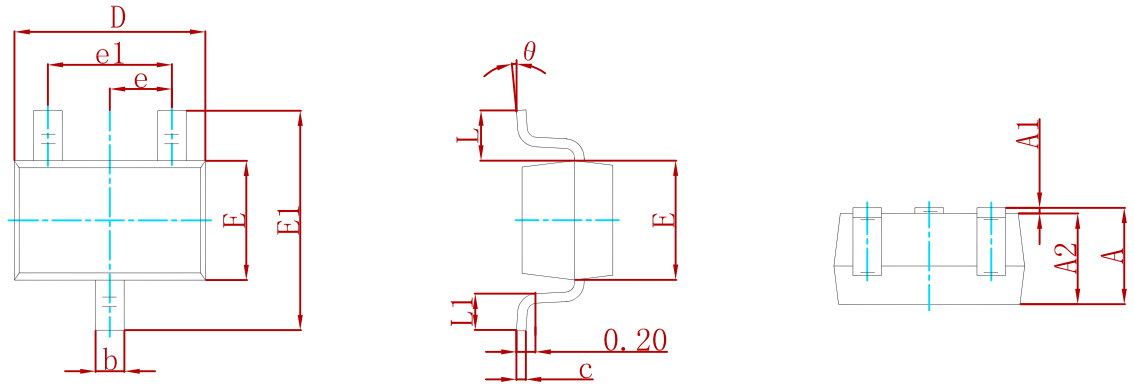
CLASSIFICATION OF h_{FE}

RANGE	100-300
MARKING	**2A**

Characteristics at T_a = 25 °C

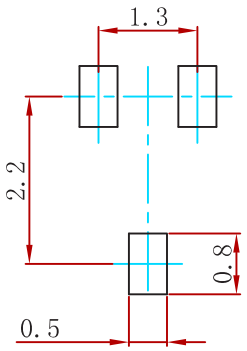
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 1 V, $-I_C$ = 0.1 mA at $-V_{CE}$ = 1 V, $-I_C$ = 1 mA at $-V_{CE}$ = 1 V, $-I_C$ = 10 mA at $-V_{CE}$ = 1 V, $-I_C$ = 50 mA at $-V_{CE}$ = 1 V, $-I_C$ = 100 mA	 h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	 60 80 100 60 30	 - - 300 - -	 - - - - -
Collector Emitter Cutoff Current at $-V_{CE}$ = 30 V	$-I_{CES}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 3 V	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C$ = 10 µA	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA	$-V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $-I_E$ = 10 µA	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 1 mA at $-I_C$ = 50 mA, $-I_B$ = 5 mA	$-V_{CE(sat)}$	- -	0.25 0.4	V
Base Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 1 mA at $-I_C$ = 50 mA, $-I_B$ = 5 mA	$-V_{BE(sat)}$	0.65 -	0.85 0.95	V
Transition Frequency at $-V_{CE}$ = 20 V, I_E = 10 mA, f = 100 MHz	f_T	250	-	MHz
Collector Output Capacitance at $-V_{CB}$ = 10 V, f = 100 KHz	C_{ob}	-	4.5	pF
Delay Time at $-V_{CC}$ = 3 V, $-V_{BE(OFF)}$ = 0.5 V, $-I_C$ = 10 mA, $-I_{B1}$ = 1 mA	t_d	-	35	ns
Rise Time at $-V_{CC}$ = 3 V, $-V_{BE(OFF)}$ = 0.5 V, $-I_C$ = 10 mA, $-I_{B1}$ = 1 mA	t_r	-	35	ns
Storage Time at $-V_{CC}$ = 3 V, $-I_C$ = 10 mA, I_{B1} = $-I_{B2}$ = -1 mA	t_{stg}	-	225	ns
Fall Time at $-V_{CC}$ = 3 V, $-I_C$ = 10 mA, I_{B1} = $-I_{B2}$ = -1 mA	t_f	-	75	ns

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBT3906W	SOT-323	3000

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